IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of:

Atty. Docket No.:

002372.00045

Takashi OHSAWA

Serial No.:

Continuation of 09/964,851, filed

Group Art Unit:

Unknown

Filed:

Herewith

September 28, 2001

Examiner:

Unknown

For:

SEMICONDUCTOR MEMORY DEVICE

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Sir:

In accordance with Applicants' duty of disclosure, the following information is submitted for consideration by the United States Patent and Trademark Office in connection with the above-captioned application. The information is identified on the attached PTO-1449 form.

This application relies, under 35 U.S.C. § 120, on the earliest filing date of prior U.S. patent application serial no. 09/964,851, filed September 28, 2001. The documents identified on the attached PTO 1449 form were submitted to and/or cited by the Office in a prior application and, therefore, copies are not required to be provided in this application. (See 37 C.F.R. § 1.98(d)).

Applicants do not waive any right to take appropriate action to establish patentability over the listed documents should they be applied as references against the claims of the present application.

It is respectfully requested that the Examiner fully consider each of the documents, initial the enclosed Form PTO-1449 in the appropriate place to indicate that the document has been

considered, and return a copy of the initialed form to the undersigned in accordance with MPEP Section 609.

Applicants believe that no fee is necessary pursuant to 37 C.F.R. § 1.97(b). However, if a fee is due, the Office is authorized to charge Deposit Account No. 19-0733.

Respectfully submitted,

BANNER & WITCOFF, LTD.

Dated: July 14, 2003

By:

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Approved for use through 10/31/2002. OMB 0651-0031

U.S. Patent and Trademark Office: U.S. DEPARTMENT OF COMMERCE

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute for form 1449A/PTO				Complete if Known		
				Application Number	TBA	
INFC	RMATION	DIS	CLOSURE	Filing Date	Herewith	
STA	STATEMENT BY APPLICANT			First Named Inventor	Takashi OHSAWA	
				Group Art Unit	Unknown	
(use as many sheets as necessary)			necessary)	Examiner Name	Unknown	
Sheet	1	of	1	Attorney Docket Number	002372.00045	

U.S. PATENT DOCUMENTS							
Examiner Initials *	Cite No. ¹	U.S. Patent Docum	nent	Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	
			Code ² (if own)				
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		5,567,959		Mineji	10-1996		
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	FOREIGN PATENT DOCUMENTS								
Examiner	Cite No. ¹	Foreign Patent Document				Name of Patentee or	Date of Publication of	Pages, Columns, Lines, Where Relevant	
Initials*		Office ³	Number ⁴	Kind Co know		Applicant of Cited Document	Cited Document MM-DD-YYYY	Passages or Relevant Figures Appear	T ₆
		JP	03-1717	68		Sakui	07-25-91		Abst
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	OTHER PRIOR ART NON PATENT LITERATURE DOCUMENTS						
Examiner Initials *	Cite No.1	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/c country where published.					
·		G. VINCENT, et al., "Electric field effect on the thermal emission of traps in semiconductor junctions", 1979 American Institute of Physics, pp. 5484-5487					
		J. LEISS, et al., "dRAM Design Using the Taper-Isolated Dynamic RAM Cell", IEEE Transactions on Electron Devices, Vol. ED-29, No. 4, April 1982, pp. 707-714					
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		H. WANN, et al., "A Capacitorless DRAM Cell on SOI Substrate", 1993 IEEE, pp. 635-638					
		P. CHATTERJEE, et al., "Memory Technology", Digest of Technical Papers, February 1979, pp. 22-23					

Examiner Signature	Date Considered	

^{*}EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.